

ABSTRACT OF THE DISCLOSUREQUASI-VERTICAL POWER SEMICONDUCTING DEVICE ON COMPOSITE  
SUBSTRATE

The invention relates to a power semiconducting device made from a semiconducting material epitaxied on a stacked structure (10) comprising a layer of semiconducting material (13) transferred onto a first face of a support substrate (11) and fixed to the support substrate by an electrically insulating layer (12), the support substrate comprising electrically conducting means between said first face and a second face, the transferred layer of semiconducting material (13) acting as an epitaxy support for the epitaxied semiconducting material (14, 15). Means (16, 17) of electrically connecting the device are provided, firstly on the epitaxied semiconducting material, and secondly on the second face of the support substrate, an electrical connection through the electrically insulating layer and said electrically conducting means of the support substrate electrically connecting the epitaxied semiconducting material (14, 15) to the electrically connecting means (17) provided on the second face of the support substrate (11).

Figure 2